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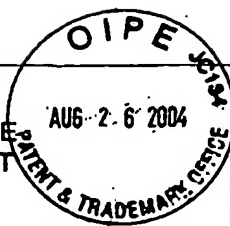
INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet A1

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Complete if Known

Application Number	10/617,843
Filing Date	July 11, 2003
First Named Inventor	Saxler
Group Art Unit	2823
Examiner Name	Fernando L. Toledo
Attorney Docket Number	5308-248

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			

OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
<i>FW</i>	1.	Ben-Yaacov et al., "AlGaIn/GaN Current Aperture Vertical Electron Transistors with Regrown Channels," <i>Journal of Applied Physics</i> . Vol. 95, No. 4, pp. 2073-2078 (2004).	
<i>FW</i>	2.	Burm et al. "Ultra-Low Resistive Ohmic Contacts on n-GaN Using Si Implantation," <i>Applied Physics Letters</i> . Vol. 70, No. 4, 464-66 (1997).	
<i>FW</i>	3.	Heikman, et al., "Mass Transport Regrowth of GaN for Ohmic Contacts to AlGaIn/GaN," <i>Applied Physics Letters</i> . Vol. 78, No. 19, pp. 2876	
<i>FW</i>	4.	Shen et al., "High-Power Polarization-Engineered GaN/AlGaIn/GaN HEMTs Without Surface Passivation," <i>IEEE Electronics Device Letters</i> . Vol. 25, No. 1, pp. 7-9 (2004).	
<i>FW</i>	5.	United States Patent Application entitled "Co-Doping for Fermi Level Control in Semi-Insulating Group III Nitrides," filed January 7, 2004 (Attorney Docket No. 5308-371).	
<i>FW</i>	6.	United States Patent Application entitled "Nitride Heterojunction Transistors Having Charge-Transfer Induced Energy Barriers and Methods of Fabricating the Same," Serial No. 10/772,882, filed February 5, 2004 (Attorney Docket No. 5308-389).	
<i>FW</i>	7.	United States Patent Application entitled "Semiconductor Devices Having a Hybrid Channel Layer, Current Aperture Transistors and Methods of Fabricating the Same," Serial No. 10/849,589, filed May 20, 2004 (Attorney Docket No. 5308-412).	
<i>FW</i>	8.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors Having Regrown Ohmic Contact Regions and Nitride-Based Transistors Having Regrown Ohmic Contact Regions," Serial No. 10/849,617, filed May 20, 2004 (Attorney Docket No. 5308-413).	
<i>FW</i>	9.	United States Patent Application entitled "Methods of Fabricating Nitride-Based Transistors with a Cap Layer and a Recessed Gate," filed July 23, 2004 (Attorney Docket No. 5308-392).	
<i>FW</i>	10.	United States Patent Application entitled "Methods of Having Laterally Grown Active Region and Methods of Fabricating Same," filed July 26, 2004 (Attorney Docket No. 5308-374).	
<i>FW</i>	11.	United States Patent Application entitled, "Silicon Carbide on Diamond Substrates and Related Devices and Methods," (Cree Docket No. P0387).	

Examiner Signature

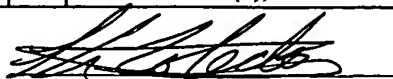
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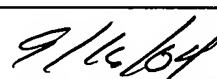
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number: 5308-248		Serial No.: 10/617,843	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Saxler et al.			
U. S. PATENT DOCUMENTS				Filing Date: July 11, 2003		Group: 2823	
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<i>Pat</i>	1.	6,586,781 B2	7/1/03	Wu et al.	257	194	
<i>Pat</i>	2.	6,548,333 B2	4/15/03	Smith	438	172	
<i>Pat</i>	3.	6,515,316 B1	2/4/03	Wojtowicz	257	194	
<i>Pat</i>	4.	6,448,648 B1	9/10/02	Boos	257	751	
<i>Pat</i>	5.	6,429,467 B1	8/6/02	Ando	257	194	
<i>Pat</i>	6.	6,046,464	4/4/00	Schetzina	257	96	
<i>Pat</i>	7.	6,028,328	2/22/00	Riechert et al.	257	194	
<i>Pat</i>	8.	5,172,197	12/15/92	Nguyen et al.	357	22	
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<i>Pat</i>	10.	4,946,547	8/7/90	Palmour et al.	156	643	
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	Document Number	Date	Country	Class	Subclass	Translation Yes No	
<i>Pat</i>	18.	WO 93/23877	11/25/93	PCT	H01L 29/10		
<i>Pat</i>	19.	10-050982	2/20/98	JP	H01L 29/778		
<i>Pat</i>	20.	0 563 847 A2	10/6/93	EP	H01L 29/812		
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<i>Pat</i>	21.	Breitschadel et al., "Minimization of Leakage Current of Recessed Gate AlGaIn/GaN HEMTs by Optimizing the Dry-Etching Process", Journal of Electronic Materials, Volume 28, No. 12, 1999.					
<i>Pat</i>	22.	Burm et al., "Recessed Gate GaN MODFETS", Solid State Electronics, Volume 41, No. 2, pp. 247-250, 1997					
<i>Pat</i>	23.	Chen et al., "Reactive ion etching for gate recessing of AlGaIn/GaN Field-effect transistors", J. Vac. Sci. Technol. B 17(6), Nov/Dec 1999					

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U. S. PATENTS & PATENT APPLICATION PUBLICATIONS							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	1	Heikman, Sten J., <i>MOCVD Growth Technologies for Applications in AlGaIn/GaN High Electron Mobility Transistors</i> , Dissertation, University of California – Santa Barbara, September 2002, 190 pages

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U. S. PATENTS & PATENT APPLICATION PUBLICATIONS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
<i>FL1</i>	1.	4,424,525	1/3/84	Mimura	357	23	
<i>FL1</i>	2.	4,471,366	9/11/84	Delagebeaudeuf et a.	357	16	
<i>FL1</i>	3.	4,727,403	2/23/88	Hilda et al.	357	22	
<i>FL1</i>	4.	4,788,156	11/98	Stoneham et al.	438	167	
<i>FL1</i>	5.	5,946,547	8/7/90	Palmour et al.	156	643	
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<i>FL1</i>	7.	5,200,022	4/6/93	Kong et al.	156	612	
<i>FL1</i>	8.	5,210,051	5/11/93	Carter, Jr.	437	107	
<i>FL1</i>	9.	5,292,501	3/8/94	Degenhardt et al.	424	49	
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<i>FL1</i>	16.	5,885,860	3/99	Weitzel et al.	438	179	
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<i>FL1</i>	21.	2001/0015446	8/23/01	Inoue et al.	257	192	
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Document Number	Date	Country	Class	Subclass	Translation Yes No		
<i>FL1</i>	22.	JP02002016087	1/18/02	Japan			
<i>FL1</i>	23.	JP02001230407	8/24/01	Japan			

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24.	WO03/049193	6/12/03	PCT				
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25.	Chu et al., "GaN materials for high power microwave amplifiers," Mat Res. Soc. Symp. Proc., Vol. 512 (1998)						
26.	Eastman et al., "Undoped AlGaIn/GaN HEMTs for Microwave Power Amplification," <i>IEEE Transactions on Electron Devices</i> , Vol. 48, No. 3, March 2001, p. 479-85.						
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29.	Gaska et al., "High-Temperature Performance of AlGaIn/GaN HFETs on SiC Substrates," <i>IEEE Electron Device Letters</i> , Vol. 18, No. 1, p. 492, October 1997						
30.	Gelmont et al., "Monte Carlo simulation of electron transport in gallium nitride," <i>J. Appl. Phys.</i> , Vol. 74, No. 3, August 1, 1993, pp. 1818-1821						
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32.	International Search Report, PCT/US02/09398, August 20, 2002						
33.	P.M. Asbeck et al., "Piezoelectric charge densities in AlGaIn/GaN HFETs," <i>Electronics Letters</i> , Vol. 33, No. 14, pp. 1230-1231, 1997						
34.	Ping et al., "DC and Microwave Performance of High-Current AlGaIn/GaN Heterostructure Field Effect Transistors Grown on P-Type SiC Substrates," <i>IEEE Electron Letters</i> , Vol. 19, No. 2, p. 54, February 1998						
35.	Sheppard et al., "Improved 10-GHz Operation of GaN/AlGaIn HEMTs on Silicon Carbide," <i>Materials Science Forum</i> , Vols. 338-342, pp. 1643-6. (2000)						
36.	Sheppard et al., "High Power Demonstration at 10 GHz with GaN/AlGaIn HEMT Hybrid Amplifiers." Presented at the 58 th DRC, Denver, CO June 2000.						
37.	Sheppard et al., U.S. Patent Application Serial No. 09/096,967 entitled, <i>Nitride Based Transistors on Semi-Insulating Silicon Carbide Substrates</i> , filed June 12, 1998.						
38.	Wu et al., "High Al-Content AlGaIn/GaN MODFET's for Ultrahigh Performance," <i>IEEE Electron Device Letters</i> , Vol. 19, No. 2, p. 50, February 1998						

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L. C. Webb

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